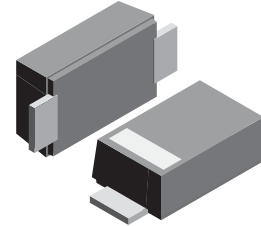


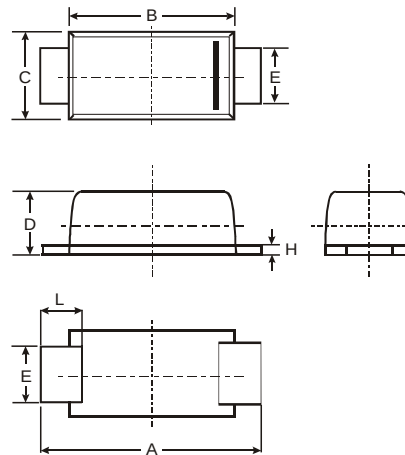
Features

- Silicon Epitaxial Planar Diode
- Fast switching diode, especially suited for applications requiring high voltage capability



Mechanical Data

- Case: SOD-123FL
plastic body over passivated junction
- Terminals: Plated axial leads,
solderable per MIL-STD-750, Method 2026
- Polarity: Color band denotes cathode end
- Marking: Any
- Weight: 0.0007 ounce, 0.02 grams



SOD-123FL			
Dim	Min	Max	Typ
A	3.50	3.90	3.70
B	2.60	3.00	2.80
C	1.63	1.93	1.78
D	0.93	1.00	0.98
E	0.85	1.25	1.00
H	0.15	0.25	0.20
L	0.55	0.75	0.65
All Dimensions in mm			

Maximum Ratings and Electrical Characteristics @ T_A = 25°C unless otherwise specified

Parameter	Test condition	Symbol	Value		Unit	
Continuous reverse voltage		V _R	240		V	
Peak repetitive reverse voltage		V _{RRM}	300		V	
Forward current (continuous)		I _F	225		mA	
Peak repetitive forward current		I _{FRM}	625		mA	
Non-repetitive peak forward current	t _p = 1 μs	I _{FSM}	4.0		A	
	t _p = 1 s	I _{FSM}	1.0		A	
Power dissipation		P _{tot}	350		mW	
Parameter	Test condition	Symbol	Min	Typ.	Max	Unit
Reverse breakdown voltage	I _R = 100 μA	V _{BR}	300			V
Leakage current	V _R = 240 V	I _R			100	nA
	V _R = 240 V, T _j = 150 °C	I _R			100	μA
Forward voltage	I _F = 20 mA	V _F		0.83	0.87	V
	I _F = 100 mA	V _F			1.00	V
Diode capacitance	V _F = V _R = 0, f = 1 MHz	C _{tot}			5.0	pF
Reverse recovery time	I _F = I _R = 30 mA, I _{rr} = 3.0 mA, R _L = 100 Ω	t _{rr}			50	ns